Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

3. Applications

Automotive and general purpose power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	23	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	98	W
Static charac	teristics		1		'		
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12		-	55	72	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 12$		-	60	75	mΩ
Avalanche ru	ggedness						
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 23 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	-	100	mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G_U: 4
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9675-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9675-100A	BUK9675-100A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω	-	100	V
V_{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	98	W
I _D	drain current	T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	16	Α
		T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	23	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	-	92	Α
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	23	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	92	Α
Avalanche i	ruggedness				'	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 23 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	100	mJ

- Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}.$ Refer to application note AN10273 for further information.

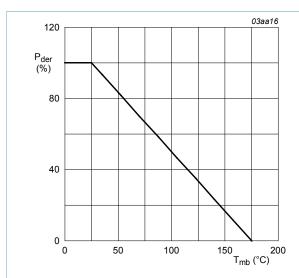


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

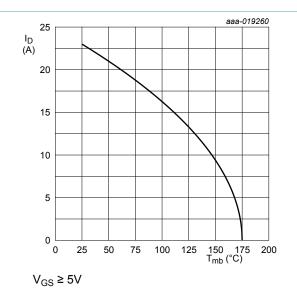
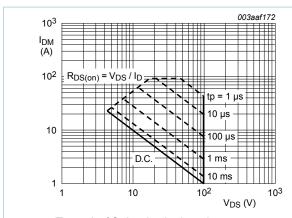


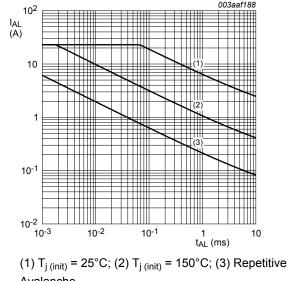
Fig. 2. Continuous drain current as a function of mounting base temperature

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 T_{mb} = 25 °C; I_{DM} is single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



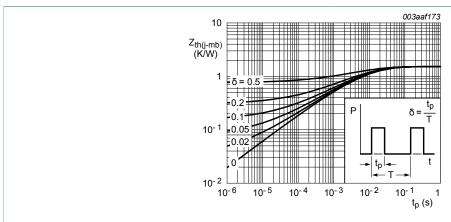
Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

Thermal characteristics

Thermal characteristics Table 6.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	1.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; FR4 board	-	50	-	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration Fig. 5.

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	100	-	-	V
brea	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.3	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 10 A; T_{j} = 25 °C; Fig. 12	-	55	72	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 175 °C;$ Fig. 13	-	-	188	mΩ
		V_{GS} = 4.5 V; I_{D} = 10 A; T_{j} = 25 °C; Fig. 12	-	61	84	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 12</u>	-	60	75	mΩ
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	24.3	-	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15	-	3	-	nC
Q_{GD}	gate-drain charge		-	12.2	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	1278	1704	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	129	155	pF
C _{rss}	reverse transfer capacitance		-	88	120	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	13	20	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	120	168	ns
t _{d(off)}	turn-off delay time		-	58	87	ns
t _f	fall time		-	57	86	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; T _j = 25 °C	-	4.5	-	nH

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		from upper edge of drain tab to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nH
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 17	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	53.7	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	126	-	nC

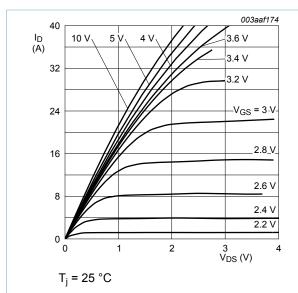


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

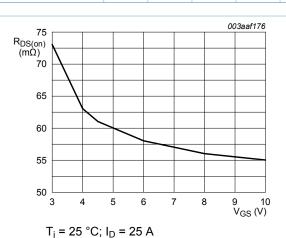


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

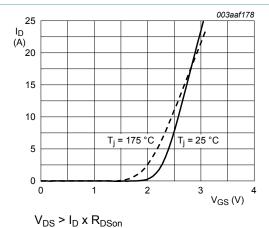


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

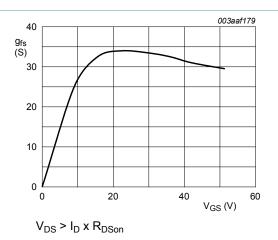


Fig. 9. Forward transconductance as a function of drain current; typical values

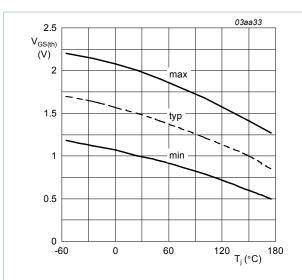


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

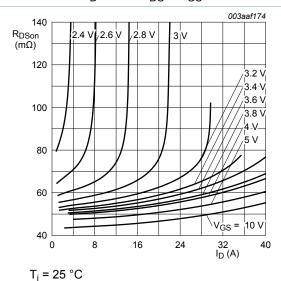
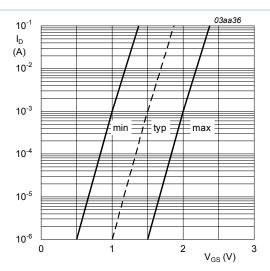


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values



 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$

Fig. 11. Sub-threshold drain current as a function of gate-source voltage

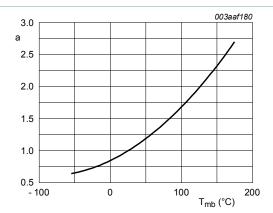


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

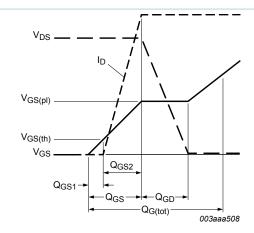
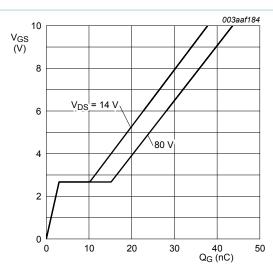


Fig. 14. Gate charge waveform definitions



 $T_j = 25 \, ^{\circ}C; I_D = 10 \, A$

Fig. 15. Gate-source voltage as a function of gate charge; typical values

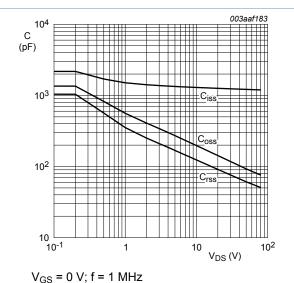


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

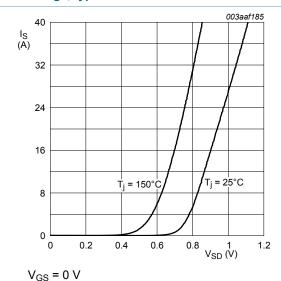
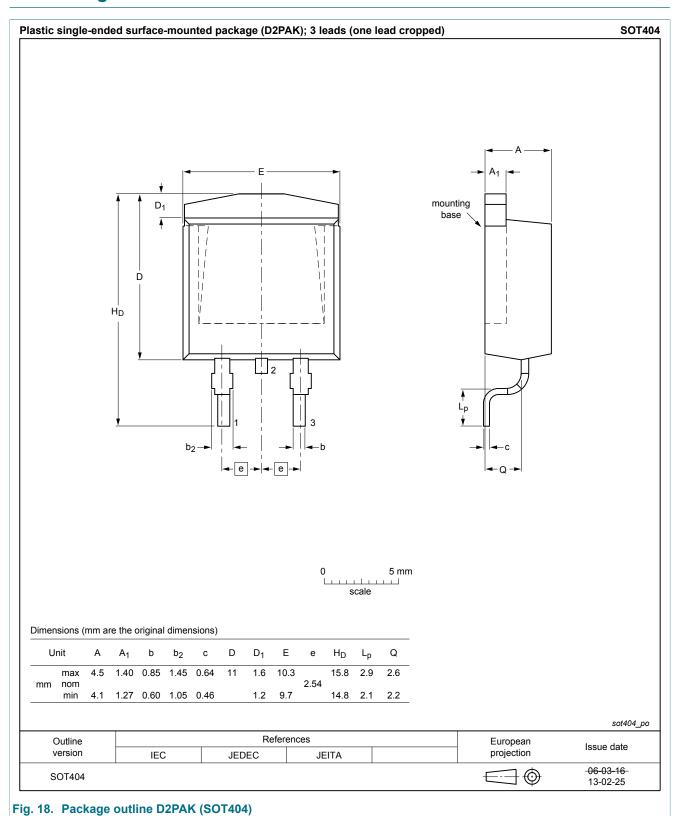


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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11. Package outline



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12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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